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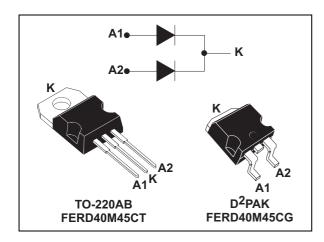




FERD40M45C

Field effect rectifier

Datasheet - production data



DescriptionThis dual rectifier

This dual rectifier is based on a proprietary technology that achieves the best in class V_F/I_R for a given silicon surface.

Packaged in TO-220AB, and D²PAK, this device is intended to be used in switch mode power supplies, or automotive applications

Table 1. Device summary

$I_{F(AV)}$	2 x 20 A
V_{RRM}	45 V
V _F (typ)	0.34 V

Features

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Low forward voltage drop
- High frequency operation

Characteristics FERD40M45C

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode at 25° C, unless otherwise stated)

Symbol	mbol Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	Forward rms current			40	Α
I _{F(AV)}	Average forward current, $\delta = 0.5$	T _c =150° C T _c =140° C	Per diode Per device	20 40	Α
I _{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinuso}$	t _p = 10 ms sinusoidal		Α
T _{stg}	Storage temperature range		-65 to + 175	°C	
T Maximum operating junction	TO-220AB, D ² PAK		175		
T _j temperature ⁽¹⁾		D ² PAK (DC forward reverse bias, t = 1 h		200	°C

^{1.} $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter	Value	Unit	
R _{th (j-c)}	Junction to case Per diode Total		1.6 1.1	°C/W
R _{th(c)}	Coupling		0.5	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_i(diode 1) = P(diode1) \times R_{th(i-c)}(Per diode) + P(diode2) \times R_{th(c)}$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25° C	V- - V			650	μΑ
'R'	Theverse leakage current	T _j = 125° C	$V_R = V_{RRM}$		25	50	mA
		T _j = 25° C	I _F = 10 A		0.38	0.415	
V _F ⁽²⁾	Forward voltage drop	$T_j = 125^{\circ} C$ $T_i = 25^{\circ} C$			0.34	0.37	v
v F. ,	Torward voltage drop			0.46	0.50		
		T _j = 125° C	I _j = 125° C		0.46	0.50	

^{1.} Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.31 \text{ x } I_{F(AV)} + 0.0095 I_{F}^{2}_{(RMS)}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

FERD40M45C Characteristics

Figure 1. Average forward power dissipation versus average forward current (per diode)

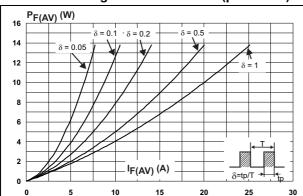


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

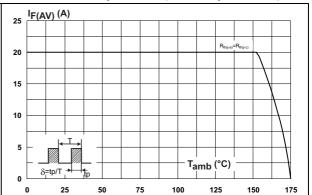
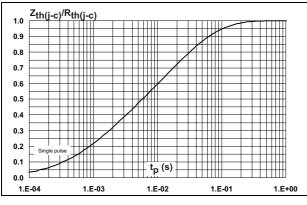


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Reverse leakage current versus reverse voltage applied (typical values, per diode)



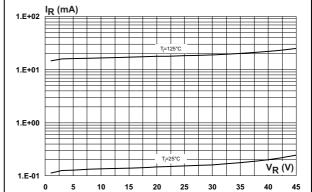
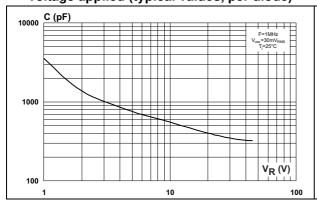
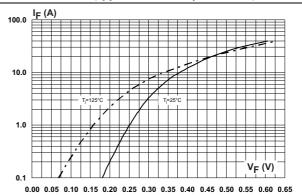


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

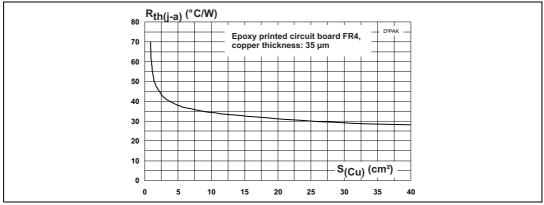
Figure 6. Forward voltage drop versus forward current (typical values, per diode)





Characteristics FERD40M45C

Figure 7. Thermal resistance junction to ambient versus copper surface under tab (typical values)



2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m (TO-220AB)

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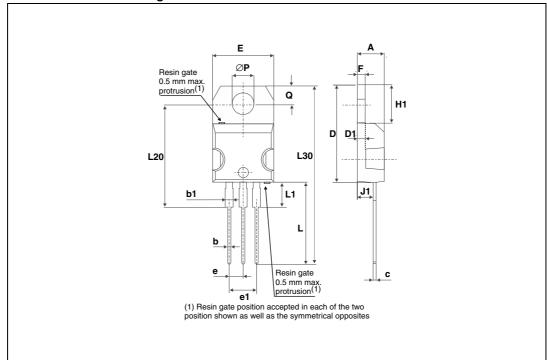


Figure 8. TO-220AB dimension definitions

Package Information FERD40M45C

Table 5. TO-220AB dimension values

	Dimensions			
Ref.	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.17	0.18
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.045	0.067
С	0.48	0.70	0.019	0.027
D	15.25	15.75	0.60	0.62
D1	1.27 typ.		0.05 typ.	
E	10	10.40	0.39	0.41
е	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.19	0.20
F	1.23	1.32	0.048	0.052
H1	6.20	6.60	0.24	0.26
J1	2.40	2.72	0.094	0.107
L	13	14	0.51	0.55
L1	3.50	3.93	0.137	0.154
L20	16.40 typ.		0.64 typ.	
L30	28.90 typ.		1.13	typ.
ØP	3.75	3.85	0.147	0.151
Q	2.65	2.95	0.104	0.116

FERD40M45C Package Information

Figure 9. D²PAK dimension definitions

Table 6. D²PAK dimension values

	Dimensions				
Ref.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
A1	2.49	2.69	0.098	0.106	
A2	0.03	0.23	0.001	0.009	
В	0.70	0.93	0.027	0.037	
B2	1.14	1.70	0.045	0.067	
С	0.45	0.60	0.017	0.024	
C2	1.23	1.36	0.048	0.054	
D	8.95	9.35	0.352	0.368	
Е	10.00	10.40	0.393	0.409	
G	4.88	5.28	0.192	0.208	
L	15.00	15.85	0.590	0.624	
L2	1.27	1.40	0.050	0.055	
L3	1.30	1.75	0.051	0.069	
М	2.29	2.79	0.090	0.110	
R	0.40 typ.		0.016 typ.		
V2	0°	8°	0°	8°	

Package Information FERD40M45C

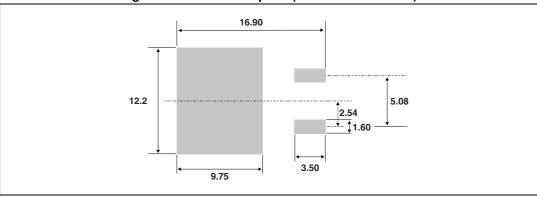


Figure 10. D²PAK footprint (dimensions in mm)

3 Ordering Information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD40M45CT	FERD40M45CT	TO-220AB	2.2 g	50	Tube
FERD40M45CG-TR	FERD40M45CG	D ² PAK	1.8 g	500	Tape and reel

4 Revision history

Table 8. Document revision history

Date	Revision	Description of Changes
13-Nov-2013	1	Initial release

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